



# IBT30N

## 10 MHz – 3.0 GHz HIGH POWER BIAS-T

REV B  
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### Key Features



- Wide Band, 10 MHz ~ 3.0 GHz
- Low Insertion Loss, 0.30 dB Typ.
- 1.22:1 VSWR
- 3000 mA DC Current Handling
- 30 W CW Power Handling
- Precision Machined Housing
- Single DC Power Supply
- Meet MIL-STD-202g

### Applications

- Up to 3.0 GHz Band
- Satellite Communications
- Broadcast
- RF Bench Tests
- Mobile Base Station



### Absolute Maximum Ratings

Parameters	Units	Ratings
DC Voltage	V	50
DC Current	mA	3000
Input Power, CW	W	30
Storage Temperature	°C	-40 ~ +85
Operating Temperature	°C	-40 ~ +85

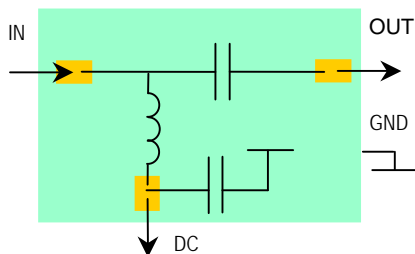
**Note: Heat sink is required for high power applications!**

### Specifications

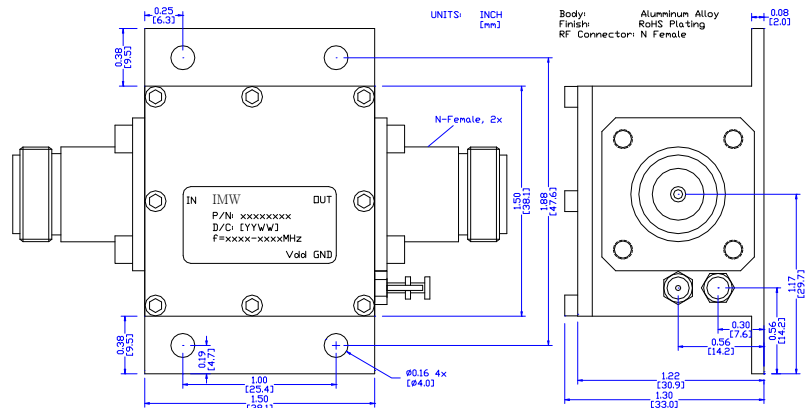
Summary of the key electrical specifications at 25°C

Index	Testing Item	Symbol	Test Constraints	Min	Typ	Max	Unit
1	Frequency Range	BW	50 Ohm Impedance	0.01		3.0	GHz
2	Insertion Loss	S <sub>21</sub>	0.01 – 3.0 GHz		0.3	1.0	dB
3	VSWR	SWR <sub>i</sub>	0.01 – 3.0 GHz		1.22:1	1.5:1	Ratio
4	Isolation, RF to DC Port		0.01 – 3.0 GHz		45		dB
5	Maximum Power Handling	P <sub>MAX</sub>	0.01 – 3.0 GHz, CW			30	W
6	Maximum DC Voltage	V <sub>DCMAX</sub>	0.01 – 3.0 GHz			50	V
7	Maximum DC Current	I <sub>DCMAX</sub>				3000	mA
8	Operating Temperature	T <sub>o</sub>		-40		+85	°C

### Functional Block Diagram



### Outline, IP-2 Housing



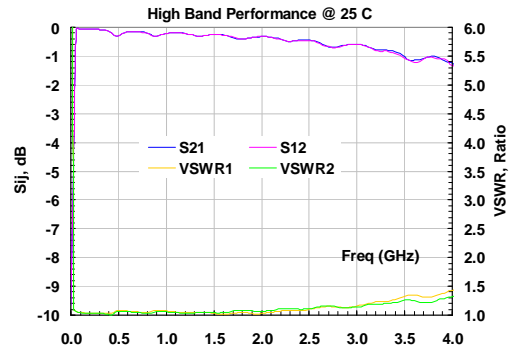
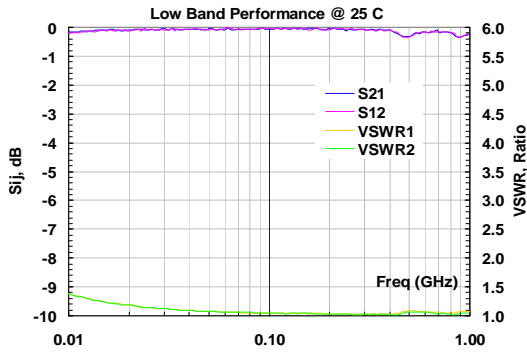
### Ordering Information

Model Number	Connectors	
	IN	OUT
IBT30N	N Female	N Female

Specifications and information are subject to change without notice.



## Typical Data



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